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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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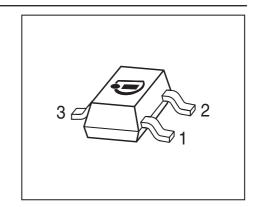


PNP Silicon High-Voltage Transistors

- Suitable for video output stages in TV sets and switching power supplies
- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary types: SMBTA42 / MMBT42 (NPN)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101







Туре	Marking	Pin Configuration			Package
SMBTA92/MMBTA92	s2D	1=B	2=E	3=C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{\sf CEO}$	300	V
Collector-base voltage	V_{CBO}	300	
Emitter-base voltage	V_{EBO}	5	
Collector current	I _C	500	mA
Base current	I_{B}	100	
Total power dissipation-	P _{tot}	360	mW
<i>T</i> _S ≤ 74 °C			
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 1 50	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 210	K/W

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¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

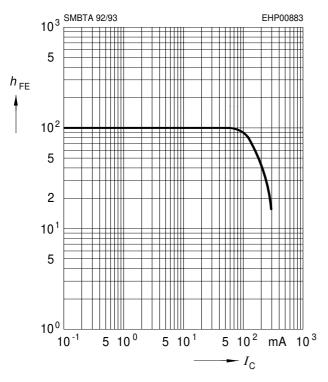
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics			1	T	
Collector-emitter breakdown voltage	V _{(BR)CEO}	300	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0					
Collector-base breakdown voltage	$V_{(BR)CBO}$	300	-	-	
$I_{\rm C} = 100 \ \mu \text{A}, \ I_{\rm E} = 0$					
Emitter-base breakdown voltage	$V_{(BR)EBO}$	5	-	-	
$I_{\rm E}$ = 100 μ A, $I_{\rm C}$ = 0					
Collector-base cutoff current	I _{CBO}				μA
$V_{\text{CB}} = 200 \text{ V}, I_{\text{E}} = 0$		-	-	0.1	
V_{CB} = 200 V, I_{E} = 0 , T_{A} = 150 °C		-	-	20	
Emitter-base cutoff current	/ _{EBO}	-	-	100	nA
$V_{\rm EB} = 5 \text{ V}, I_{\rm C} = 0$					
DC current gain ¹⁾	h _{FE}				-
$I_{\rm C}$ = 1 mA, $V_{\rm CE}$ = 10 V		25	-	-	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 10 V		40	-	-	
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 10 V		25	-	-	
Collector-emitter saturation voltage ¹⁾	V _{CEsat}	-	-	0.5	V
$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 2 mA					
Base emitter saturation voltage ¹⁾	V _{BEsat}	-	-	0.9	
$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 2 mA					
AC Characteristics				•	•
Transition frequency	f _T	50	_	-	MHz
$I_{\rm C}$ = 20 MHz, $V_{\rm CE}$ = 10 V, f = 100 MHz					
Collector-base capacitance	C _{cb}	-	-	6	pF
$V_{CB} = 20 \text{ V}, f = 1 \text{ MHz}$					

¹Pulse test: $t < 300\mu s$; D < 2%



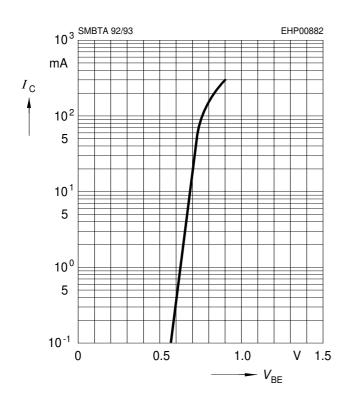
DC current gain $h_{FE} = f(I_C)$

$$V_{CE}$$
 = 10 V



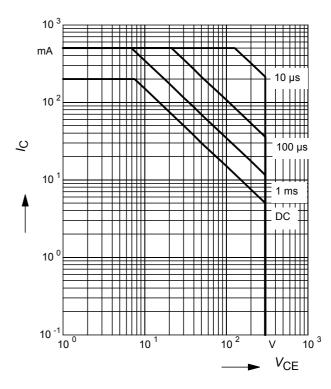
Collector current $I_{C} = f(V_{BE})$

$$V_{CE} = 10V$$



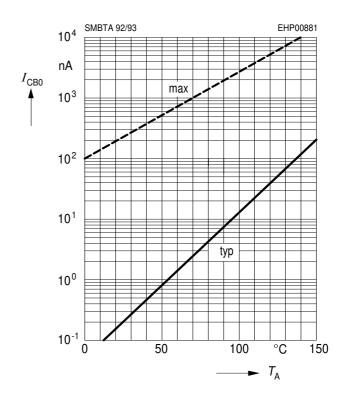
Operating range $I_{C} = f(V_{CEO})$

$$T_{A} = 25^{\circ}\text{C}, D = 0$$



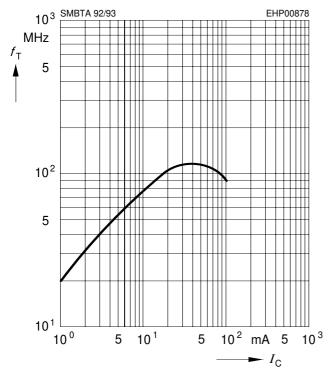
Collector cutoff current $I_{CBO} = f(T_A)$

$$V_{\rm CBO}$$
 = 200 V

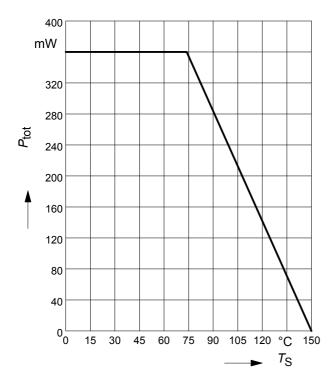




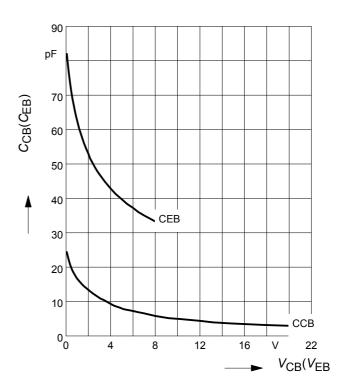
Transition frequency $f_T = f(I_C)$



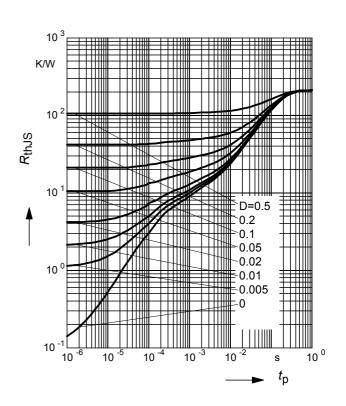
Total power dissipation $P_{tot} = f(T_S)$



Collector-base capacitance $C_{\text{cb}} = f(V_{\text{CB}})$ Emitter-base capacitance $C_{\text{eb}} = f(V_{\text{EB}})$



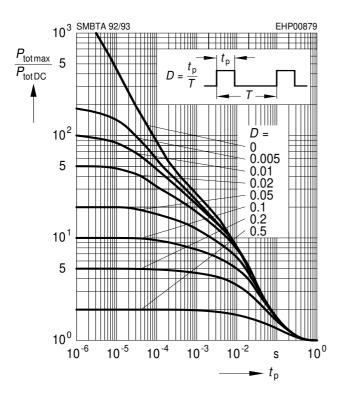
Permissible Pulse Load $R_{thJS} = f(t_p)$





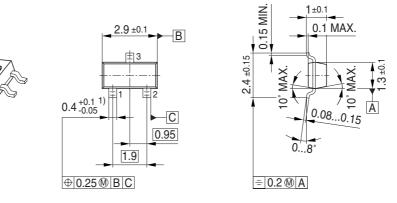
Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$



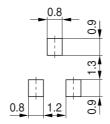


Package Outline

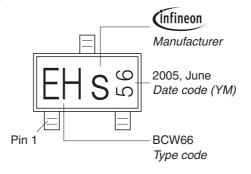


1) Lead width can be 0.6 max. in dambar area

Foot Print

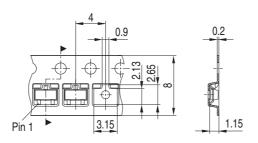


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel



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